

HIGH ELECTRON MOBILITY TRANSISTOR

Abstract of Disclosure

A high electron mobility transistor (HEMT) includes a first doped layer disposed in a substrate, a mesa isolation disposed on the substrate, a gate electrode disposed on the mesa isolation, a source electrode and a drain electrode disposed adjacent to two sides of the gate electrode, a passivation layer disposed on the mesa isolation and around the source electrode and the drain electrode, a first metal line connecting the source electrode and the first doped layer, and a second metal line connecting the drain electrode and the first doped layer.

Figure 1